

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	14094	((257/49) or (257/52) or (257/55) or (257/56) or (257/57) or (257/58) or (257/59) or (257/62) or (257/63) or (257/72) or (257/200) or (257/201) or (257/213) or (257/288) or (257/390) or (257/403) or (257/406) or (257/410) or (257/411)).OCL.S.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/05/26 16:05
L2	0	1 and (source drain gate). clm. and ("Zn.sub.2" near1 "SnO.sub.4" spinel near1 (zinc adj stannate)).clm.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/26 16:07
L3	0	((hoffman near1 randy).in. (chiang near1 hai).in. (wager near1 john).in. (hewlett near1 packard). as.) and (source drain gate).clm. and ("Zn.sub.2" near1 "SnO.sub.4" spinel near1 (zinc adj stannate) ZTO).clm.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/26 16:09
L4	0	1 and (source drain gate). ti,ab,clm. and ("Zn.sub.2" near1 "SnO.sub.4" spinel near1 (zinc adj stannate)). ti,ab,clm.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/26 16:09
L5	0	1 and (source drain gate) and ("Zn.sub.2" near1 "SnO.sub.4" spinel near1 (zinc adj stannate)).ti,ab, clm.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/26 16:10
L6	0	1 and (source drain gate) and ("Zn.sub.2" near1 "SnO.sub.4" spinel near1 (zinc adj stannate)).ti,ab, clm.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/26 16:10
S1	3	((("5,470,768") or ("5,879,973") or ("6,569,720")).PN.	USPAT; EPO; JPO; IBM_TDB	OR	OFF	2006/05/31 15:33

S2	20	((("20036013261") or ("6561174") or ("20030104659") or ("20030139026") or ("20030180996") or ("20030186489") or ("20030207502") or ("20030218221") or ("20030218222") or ("20030219530") or ("20030224550"))).PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/01 16:48
S3	10	((("20036013261") or ("6561174") or ("20030104659") or ("20030139026") or ("20030180996") or ("20030186489") or ("20030207502") or ("20030218221") or ("20030218222") or ("20030219530") or ("20030224550"))).PN.	US-PGPUB; USPAT	OR	OFF	2005/10/01 16:53
S4	1	("20030013261").PN.	US-PGPUB; USPAT	OR	OFF	2005/10/01 16:52
S5	11	S3 S4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/01 16:53
S6	9	((("4559238") or ("4589026") or ("4887255") or ("5107314") or ("5744864") or ("6255130") or ("6255655") or ("6362499") or ("6391462"))).PN. or ((2002/0153587) or (2002/0171085)).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/10/01 16:56
S7	11	((("4559238") or ("4589026") or ("4887255") or ("5107314") or ("5744864") or ("6255130") or ("6255655") or ("6362499") or ("6391462") or ("20020153587") or ("20020171085"))).PN.	US-PGPUB; USPAT	OR	OFF	2005/10/01 16:57

S8	0	ep-0040076\$-\$\$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/01 16:58
S9	0	ep-0040076\$-\$\$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/01 16:59
S10	82	sasano.in.	EPO	OR	OFF	2005/10/01 17:02
S11	0	sasano.in. and drain and compound	EPO	OR	OFF	2005/10/01 17:01
S12	0	sasano.in. and drain	EPO	OR	OFF	2005/10/01 17:02
S13	4	sasano.in. and semiconductor	EPO	OR	OFF	2005/10/01 17:02
S14	1	(EP-40076-\$).did.	EPO	OR	OFF	2005/10/01 17:08
S15	4	((("5,744,864") or ("20020101557"))).PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/01 17:08
S16	2	((("5,744,864") or ("20020101557"))).PN.	US-PGPUB; USPAT	OR	OFF	2005/10/01 17:08
S17	4	"763353".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/31 11:40
S18	4	"763353".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/31 11:42
S19	2	"20040127038".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/31 11:51
S20	5	"2004023432".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/31 11:52

S21	2	"20040023432".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/31 11:53
S22	4	S19 S21	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/31 11:55
S23	2	jp-2003086808\$-\$\$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/31 11:56
S24	2	("20030047785").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/31 11:56
S25	0	Garcia.in. and ("Zn.sub.2" near1 "Sn" near1 "O. sub.4")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/31 12:44
S26	0	("257"/\$7.ccls. "438"/\$7. ccls. "117"/\$7.ccls.) and ("Zn.sub.2" near1 "Sn" near1 "O.sub.4") near10 (semiconductor channel)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/31 12:45
S27	3	("257"/\$7.ccls. "438"/\$7. ccls. "117"/\$7.ccls.) and (zinc adj stannate "Zn. sub.2" near1 "Sn" near1 "O.sub.4") near10 (semiconductor channel)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/31 12:48
S28	10	(zinc adj stannate "Zn. sub.2" near1 "Sn" near1 "O.sub.4") near10 (semiconductor channel)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/31 12:49
S29	2	(zinc adj stannate "Zn. sub.2" near1 "Sn" near1 "O.sub.4") near10 (semiconductor channel) and (MOSFET MOS MISFET MESFET JFET NMOS NMOSFET PMOS PMOSFET field adj effect gate transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/31 12:50

S30	0	(zinc adj stannate "Zn.sub.2" near1 "Sn" near1 "O.sub.4") near10 (semiconductor channel) and (MOSFET MOS MISFET MESFET JFET NMOS NMOSFET PMOS PMOSFET field adj effect gate transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/31 13:02
S31	0	(zinc adj stannate "Zn.sub.2" near1 "Sn" near1 "O.sub.4" cubic adj spinel) near10 (semiconductor channel) and (MOSFET MOS MISFET MESFET JFET NMOS NMOSFET PMOS PMOSFET field adj effect gate transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/31 13:02
S32	0	(zinc adj stannate "Zn.sub.2" near1 "Sn" near1 "O.sub.4" zinc adj spinel) near10 (semiconductor channel) and (MOSFET MOS MISFET MESFET JFET NMOS NMOSFET PMOS PMOSFET field adj effect gate transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/31 13:10
S33	324	transparent near1 (thin adj film adj transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/31 13:11
S34	0	(transparent near1 (thin adj film adj transistor tft) tft) and ("Zn.sub.2" near1 "Sn" near1 "O.sub.4")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/31 13:12
S35	0	((transparent near1 (thin adj film adj transistor tft) tft) and ("Zn.sub.2" near1 "Sn" near1 "O.sub.4"))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/31 13:12
S36	0	alumin\$1um adj titanate near6 gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/31 15:33

S37	9707	("AIO.sub."\$4 "TiO.sub."\$4 "Al.sub."\$4 alumin\$1um adj titanate titanium adj aluminate) and gate and (transistor field adj effect MOSFET MOS NMOS PMOS NMOSFET PMOSFET NMISFET PMISFET PMIS TFT thin adj film adj (transistor OTFT)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 09:58
S38	115	((("TiO.sub."\$4 near4 "AIO.sub."\$4) (alumin\$1um adj titanate) (titanium adj aluminate)) and gate and (transistor field adj effect MOSFET MOS NMOS PMOS NMOSFET PMOSFET NMISFET PMISFET PMIS TFT thin adj film adj (transistor OTFT)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 10:00
S39	79	((("TiO.sub."\$4 near4 "AIO.sub."\$4) (alumin\$1um adj titanate) (titanium adj aluminate)) and gate and (transistor field adj effect MOSFET MOS NMOS PMOS NMOSFET PMOSFET NMISFET PMISFET PMIS TFT thin adj film adj (transistor OTFT) and @ad< "20030726"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 10:03
S40	0	((("TiO.sub."\$4 near4 "AIO.sub."\$4) (alumin\$1um adj titanate) (titanium adj aluminate)) near15 gate and (transistor field adj effect MOSFET MOS NMOS PMOS NMOSFET PMOSFET NMISFET PMISFET PMIS TFT thin adj film adj (transistor OTFT) and @ad< "20030726"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/02 10:16
S41	4	"763353".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/01 11:39
S42	706	((alumin\$1um adj oxide) ("Al.sub."\$3 near1 (O "O.sub."\$3)) "AIO.sub."\$3) near8 (titanium adj oxide) ("Ti.sub."\$3 near1 (O "O.sub."\$3)) "TiO.sub."\$3) same gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 11:52

S43	131	((alumin\$1um adj oxide) ("Al.sub."\$3 near1 (O "O. sub."\$3)) "AlO.sub."\$3) near8 (titanium adj oxide ("Ti.sub."\$3 near1 (O "O. sub."\$3)) "TiO.sub."\$3) near10 gate near10 (dielectric insulati\$2)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 11:53
S44	66	((alumin\$1um adj oxide) ("Al.sub."\$3 near1 (O "O. sub."\$3)) "AlO.sub."\$3) near8 (titanium adj oxide ("Ti.sub."\$3 near1 (O "O. sub."\$3)) "TiO.sub."\$3) near10 gate near10 (dielectric insulati\$2)	USPAT	OR	ON	2006/06/01 11:53
S45	2	"20050253157".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/01 15:47
S46	140	rf adj sputtering near6 amorphous	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/01 15:47
S47	0	(zno zinc adj oxide) near10 (rf adj sputtering near6 amorphous)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 15:48
S48	16	(oxide) near10 (rf adj sputtering near6 amorphous)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 15:50
S49	259	(oxide) near10 (sputtering near6 amorphous)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 15:50
S50	19	(zinc adj oxide zno) near10 (sputtering near6 amorphous)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 15:51
S51	1	(US-20050017244-\$.did.	US-PGPUB	OR	OFF	2006/06/01 16:10
S52	1	S51 and transparent	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 16:10

S53	0	dissocation adj constant near5 (zinc adj stannate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 16:17
S54	0	dissocation adj constant near5 ("Zn.sub.2" near1 "Sn" near1 "O.sub.4") (zinc adj stannate))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 16:40
S55	0	(indium-tin-oxide indium adj tin adj oxide ITO) and "20040127038".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 17:16
S56	11	drain-to-gate near4 bias	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 17:24
S57	1894	drain near2 connect\$2 near2 gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 17:25
S58	7956	drain near1 connect\$3 near1 gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 17:25
S59	571	drain near1 connect\$3 near1 gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 17:33
S60	49	back adj gate and gate-to- drain	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 17:34
S61	2	back adj gate and gate-to- drain and (tft thin adj film adj transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 17:35
S62	2	back adj gate and gate-to- drain and (otft tft thin adj film adj transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 17:35

S63	2	(back adj gate back-gate) and gate-to-drain and (otft tft thin adj film adj transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 17:36
S64	334	(back adj gate back-gate) and (otft tft thin adj film adj transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 17:36
S65	267	(back adj gate back-gate) and (otft tft thin adj film adj transistor) and circuit	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 18:02
S66	29	hot adj electron.ti,ab,clm. and gate-to-drain	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 18:05
S67	585	hot adj electron.ti.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 18:11
S68	40	hot adj electron adj effect. ti.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 18:14
S69	18	hot adj electron adj effect. ti. and gate near5 drain	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 18:15
S70	1	(US-20050017244-\$).did.	US-PGPUB	OR	OFF	2006/06/02 08:40
S71	0	S70 and means	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/02 08:41
S72	1	(US-20050017244-\$).did.	US-PGPUB	OR	OFF	2006/06/02 08:41
S73	0	S70 and "means"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/02 08:41

S74	524	(thin adj film adj transistor tft).ti,ab,clm. and (indium-tin ITO) near8 source and (indium-tin ITO) near8 drain	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/02 09:41
S75	54	(thin adj film adj transistor tft).ti,ab,clm. and (indium-tin ITO) near2 source and (indium-tin ITO) near2 drain	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/02 09:41
S76	41	(US-20050104508-\$ or US-20040066484-\$ or US-20030185266-\$ or US-20050017244-\$ or US-20030207502-\$ or US-20030224550-\$ or US-20030219530-\$ or US-20030218222-\$ or US-20030218221-\$ or US-20030186489-\$ or US-20030139026-\$ or US-20030104659-\$ or US-20030180996-\$ or US-20030013261-\$ or US-20020171085-\$ or US-20020153587-\$ or US-20040127038-\$ or US-20040023432-\$ or US-20030047785-\$).did. or (US-4521698-\$ or US-6569720-\$ or US-6561174-\$ or US-6391462-\$ or US-6362499-\$ or US-5744864-\$ or US-5107314-\$ or US-4887255-\$ or US-4589026-\$ or US-5879973-\$ or US-5470768-\$ or US-6255655-\$ or US-6255130-\$ or US-4559238-\$ or US-6653206-\$ or US-6617609-\$ or US-7017830-\$).did. or (EP-40076-\$).did. or (JP-2003086808-\$).did. or (WO-200217368-\$ or WO-200403449-\$ or US-20030047785-\$).did.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2006/06/02 10:16

S77	0	((("TiO.sub."\$4 near4 "AlO.sub."\$4) (alumin\$1um adj titanate) (titanium adj aluminate)) near15 gate and (transistor field adj effect MOSFET MOS NMOS PMOS NMOSFET PMOSFET NMISFET PMISFET PMIS TFT thin adj film adj transistor OTFT) and @ad< "20030726" and S76	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/02 10:17
S78	0	("AlO.sub."\$3 "A.sub.2O.sub.3") near10 ("TiO.sub."\$72 "TiO.sub.2") near10 ((insulati\$2 dielectric) near2 gate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/02 10:25
S79	69580	("Al.sub."\$1 near1 "O.sub."\$1)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/02 10:26
S80	0	("Al.sub."\$1 near1 "O.sub."\$1) near20 ("Ti.sub."\$1 near1 "O.sub."\$1) near20 gate near20 (dielectric insulati\$2) near20 (combination multi-layer\$2 multilayer\$2)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/02 10:28
S81	0	("Al.sub."\$1 near1 "O.sub."\$1) near20 ("Ti.sub."\$1 near1 "O.sub."\$1) near20 gate near20 (dielectric insulati\$2)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/02 10:28
S82	87	((("Al.sub."\$1 near1 "O.sub."\$1) "AlO.sub."\$1) near20 (("Ti.sub."\$1 near1 "O.sub."\$1) "TiO.sub."\$1) near20 gate near20 (dielectric insulati\$2)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/02 10:30
S83	0	((("Al.sub."\$1 near1 "O.sub."\$1) "AlO.sub."\$1) near20 (("Ti.sub."\$1 near1 "O.sub."\$1) "TiO.sub."\$1) near20 gate near20 (dielectric insulati\$2) near20 mixture	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/02 10:30
S84	1	((("Al.sub."\$1 near1 "O.sub."\$1) "AlO.sub."\$1) near20 (("Ti.sub."\$1 near1 "O.sub."\$1) "TiO.sub."\$1) near20 gate near20 (dielectric insulati\$2) near20 mixture	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/02 10:35

S85	9	((("Al.sub."\$1 near1 "O.sub."\$1) "AlO.sub."\$1) near20 (("Ti.sub."\$1 near1 "O.sub."\$1) "TiO.sub."\$1) near20 gate near20 (dielectric insulat\$2) near20 (combination mixture multi-layer multi adj layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/02 10:42
S86	0	((("Al.sub."\$1 near1 "O.sub."\$1) "AlO.sub."\$1) near20 (("Ti.sub."\$1 near1 "O.sub."\$1) "TiO.sub."\$1) near20 gate near20 (dielectric insulat\$2) near20 (combination mixture multi-layer multi adj layer) and (thin adj film adj transistor tft oftt)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/02 10:43
S87	9	((("Al.sub."\$1 near1 "O.sub."\$1) "AlO.sub."\$1) near20 (("Ti.sub."\$1 near1 "O.sub."\$1) "TiO.sub."\$1) near20 gate near20 (dielectric insulat\$2) near20 (combination mixture multi-layer multi adj layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/02 10:53
S88	9	((("Al.sub."\$1 near1 "O.sub."\$1) "AlO.sub."\$1) (alumin\$1um adj titanate) (titanium adj aluminate)) near20 (("Ti.sub."\$1 near1 "O.sub."\$1) "TiO.sub."\$1) near20 gate near20 (dielectric insulat\$2) near20 (combination mixture multi-layer multi adj layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/02 10:55
S89	9	((("Al.sub."\$3 near1 "O.sub."\$3) "AlO.sub."\$3) (alumin\$1um adj titanate) (titanium adj aluminate)) near20 (("Ti.sub."\$3 near1 "O.sub."\$3) "TiO.sub."\$3) near20 gate near20 (dielectric insulat\$2) near20 (combination mixture multi-layer multi adj layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/02 12:48
S90	209	((("Al.sub."\$3 near1 "O.sub."\$3) "AlO.sub."\$3) near20 (("Ti.sub."\$3 near1 "O.sub."\$3) "TiO.sub."\$3) near20 barrier	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/02 12:49

S91	5	((("Al.sub."\$3 near1 "O.sub."\$3) "AlO.sub."\$3) near20 ((("Ti.sub."\$3 near1 "O.sub."\$3) "TiO.sub."\$3) near20 barrier near20 gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/02 12:52
S92	0	((("Al.sub."\$3 near1 "O.sub."\$3) "AlO.sub."\$3) near20 (cap adj (layer film)) near20 gate near20 (semiconductor channel)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/02 12:53
S93	3	((alumin\$1um adj oxide) ("Al.sub."\$3 near1 (O "O.sub."\$3)) "AlO.sub."\$3) near8 (cap adj layer) near20 gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/02 12:59
S94	1839	((alumin\$1um adj oxide) ("Al.sub."\$3 near1 (O "O.sub."\$3)) "AlO.sub."\$3) near4 barrier	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/02 12:59
S95	45	((alumin\$1um adj oxide) ("Al.sub."\$3 near1 (O "O.sub."\$3)) "AlO.sub."\$3) near4 barrier near4 (Ti titanium)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/02 13:03
S96	27	((alumin\$1um adj oxide) ("Al.sub."\$3 near1 (O "O.sub."\$3)) "AlO.sub."\$3) near4 barrier near4 (Ti titanium) and gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/02 13:03
S97	11320	((257/49) or (257/52) or (257/55) or (257/56) or (257/57) or (257/58) or (257/59) or (257/62) or (257/63) or (257/72) or (257/200) or (257/201) or (257/213) or (257/288) or (257/390) or (257/403) or (257/406) or (257/410) or (257/411)).OCL.S	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/02 14:32
S98	0	S97 and ((alumin\$1um adj titanate) (titanium adj aluminate) ("Al.sub."\$2 near1 "O.sub."\$2 "AlO.sub."\$2 alumin\$1um adj oxide)) near20 ("Ti.sub."\$2 near1 "O.sub."\$2 near1 "TiO.sub."\$2 (titanium adj oxide)) near20 gate and (channel semiconductor) near4 ((("Zn.sub."\$2 near1 "SnO.sub."\$2) ((("Zn.sub."\$2 near1 "O") near10 ("SnO.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/02 14:47

		sub."\$2)))				
S99	8	((("6836540") or ("6998656") or ("6940097") or ("7026713")).PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/02 14:49
S100	45	randy near1 hoffman.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/02 14:49
S101	26	randy near1 hoffman.in. and (zinc adj oxide ZnO ("Zn.sub.2" near1 "O")) and (Ti titanium) and (Al alumin\$1um)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/02 14:51
S102	89	(hewlett.as. hoffman.in. (hai near1 chiang).in.) (john near2 wager).in.) and (zinc tin) adj oxide.ti, ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/14 11:09
S103	2	(hewlett.as. hoffman.in. (hai near1 chiang).in.) (john near2 wager).in.) and (zinc tin) adj oxide.ti, ab,clm. and stannate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/14 11:10
S104	18	(hewlett.as. hoffman.in. (hai near1 chiang).in.) (john near2 wager).in.) and (zinc tin) adj oxide.ti, ab,clm. and (stannate "SnO.sub."\$2)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/14 11:10
S105	2	"20040127038".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/07/14 12:05
S106	1	(US-20050017244-\$.)did.	US-PGPUB	OR	OFF	2007/11/14 15:31
S107	0	(US-20050017244-\$.)did. and means	US-PGPUB	OR	ON	2007/11/14 15:31
S108	1743	(aluminum adj oxide) and strontium adj oxide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/14 19:15
S109	7	"410830".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/15 10:27

S110	2	("20040127038").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/11/15 13:26
S111	0	("533453.ap.").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/11/15 14:15
S112	2	("20020172317").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/11/15 14:18
S113	2	("4093886").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/11/15 14:53
S114	0	wo-9108180\$-\$did.	USPAT	OR	OFF	2007/11/15 14:54
S115	2	wo-9108180\$-\$did.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/11/15 16:23
S116	32	percentage near3 porosity near3 "%"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/15 16:24
S122	2	"20040127038".pn.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/11/21 10:03
S123	2	"4521698".PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/11/21 10:05

S124	2	"6674495".PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/11/21 10:05
S125	13	"6100558"	USPAT	OR	OFF	2007/11/21 10:50
S126	1	("6100558").PN.	USPAT; USOCR	OR	OFF	2007/11/21 10:52
S127	2	("20040169210").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/11/21 10:53
S128	2	("6184946").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/11/21 10:53
S129	0	("20060183274").PN.	USPAT; USOCR	OR	OFF	2007/11/22 08:36
S130	9	carcia.in. and thin adj film adj transistor	US-PGPUB; USPAT	OR	ON	2007/11/22 08:44
S131	6	thin adj film adj transistor and (zinc-tin adj oxide zto) near4 channel	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/22 08:49
S132	7	(tft thin adj film adj transistor) and (zinc-tin adj oxide zto) near8 channel	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/22 08:50
S133	11	(tft thin adj film adj transistor) and (zinc-tin adj oxide zto zinc near1 tin near1 oxide) near8 channel	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/22 08:52
S134	12	(tft thin adj film adj transistor mos mosfet) and (zinc-tin adj oxide zto zinc near1 tin near1 oxide) near8 channel	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/22 08:53

S135	10	(mos mosfet) and (zinc-tin adj oxide zto zinc near1 tin near1 oxide) near8 channel	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/22 08:53
S136	11	(mosfet transistor) and (zinc-tin adj oxide zto zinc near1 tin near1 oxide) near8 channel	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/22 08:56
S137	11	(mosfet transistor) and (zinc-tin adj oxide zto zinc near1 tin near1 oxide "zno: sn") near8 channel	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/22 09:03
S138	0	("20050017244").PN.	USPAT; USOCR	OR	OFF	2007/11/22 09:03
S139	2	("20050017244").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/11/22 09:06
S140	2	"20060284171"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/11/22 09:11
S141	10	zinc near1 tin near1 oxide near10 channel	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/11/22 09:12
S142	2	zinc near1 tin near1 oxide near10 channel not hoffman.in.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/22 09:32
S143	12023	zinc near2 tin near2 oxide zito zto "zno:sn" "sno"\$3"zn"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/22 09:33

S144	26	(zinc near2 tin near2 oxide zto zto "zno:sn" "sno"\$3"zn") near4 channel	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/22 09:44
S145	0	zno near4 sno\$1 near4 (mixture combination) near10 channel and transistor	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/22 09:45
S146	0	zno near4 sno\$1 near8 (mixture combination) near10 channel and transistor	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/22 09:45
S147	5	(zinc adj oxide zno) near4 (tin adj oxide sno\$1) near8 (mixture combination) near10 channel and transistor	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/22 09:50
S148	31	(zinc adj oxide zno) near4 (tin adj oxide sno\$1) near10 channel and transistor	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/22 09:59
S149	1	(zinc-tin- adj oxide zinc adj tin adj oxide) near20 channel.dlm.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/22 10:03
S150	2	"20040023432".pn.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/22 10:07
S151	2	jp-2003088808\$.did.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/22 10:10

S152	0	ohtomo.in. and zto	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/22 10:11
S153	0	ohtomo.in. and (zinc-tin-oxide zto)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/22 10:11
S154	0	(ohtomo.in. kawasaki.in.) and (zinc-tin-oxide zto)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/22 10:17
S155	23	"5470788"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/22 10:18
S156	3	((("5470788") or ("5879973") or ("6569720")).PN.	USPAT; USOCR	OR	OFF	2007/11/22 10:24
S157	3	((("5470768") or ("5879973") or ("6569720")).PN.	USPAT; USOCR	OR	OFF	2007/11/22 10:30
S158	11	((("4559238") or ("4589026") or ("4887255") or ("5107314") or ("5744864") or ("6255130") or ("6255655") or ("6362499") or ("6391462") or ("20020153587") or ("20020171085")).PN.	US-PGPUB; USPAT	OR	OFF	2007/11/22 10:31
S159	2	("20040127038").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/11/23 13:10
S160	13987	"SnO.sub.2"	USPAT	OR	OFF	2007/11/23 07:02
S161	0	"SnO.sub.2" near10 "ZnO" near10 (combination mixture) near20 channel and transistor	USPAT	OR	ON	2007/11/23 07:03

S162	4	"SnO.sub.2" near10 "ZnO" near10 (combination mixture) same channel and transistor	USPAT	OR	ON	2007/11/23 08:41
S163	2	jp-60198861\$-\$\$.did.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/23 08:41
S164	1214	sputtering near4 ("SnO.sub.2" "ZnO")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/11/23 13:11
S165	211	sputtering near4 ("SnO.sub.2" "ZnO") and channel and semiconductor	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/11/23 13:11
S166	4	sputtering near4 ("SnO.sub.2" "ZnO") and channel and semiconductor and (Carcia.in. Glessen.in.)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/23 13:55
S167	1	("6,100,558").PN.	USPAT; USOCR	OR	OFF	2007/11/23 14:41
S168	13512	((257/49) or (257/52) or (257/55) or (257/56) or (257/57) or (257/58) or (257/59) or (257/62) or (257/63) or (257/72) or (257/200) or (257/201) or (257/213) or (257/288) or (257/390) or (257/403) or (257/406) or (257/410) or (257/411)).CCL.S.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/11/23 14:42
S169	6	S168 and (thin adj film adj transistor tft) and (zinc-tin-oxide Zn-Sn-oxide (ZnO near10 "SnO.sub.2") ("Zn.sub.2" near1 "SnO.sub.4") zinc adj stann?te "ZnSnO.sub.3") near20 channel	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/23 14:46

S170	3	((randy near2 hoffman).in. (hai near2 chiang).in. (john near2 wager).in. hewlett.as. oregon.as.) and (thin adj film adj transistor tft).dm. and (zinc-tin-oxide Zn-Sn-oxide (ZnO near10 "SnO.sub.2") ("Zn.sub.2" near1 "SnO. sub.4") zinc adj stann?te "ZnSnO.sub.3") near20 channel.dm.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/23 14:48
S171	2	"20040127038".pn.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/08 09:46
S172	423	non-stoichiometric adj compound	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/08 10:53
S173	2	"2003185266".pn.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/08 14:01
S174	2	"20030185266".pn.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/08 14:02
S175	1	"20030185266".pn. and (sputter sputtering)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/08 14:03
S176	0	sputtering near10 amorphous near10 zinc-tin- oxide	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/08 16:05
S177	0	sputtering near10 crystalline near10 zinc-tin- oxide	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/08 16:05

S178	0	sputtering near10 crystal near10 zinc-tin-oxide	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/08 16:05
S179	4961	sputtering near10 crystal	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/08 16:05
S180	2624	sputtering near5 crystal	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/08 16:06
S181	632	method near5 sputtering near5 crystal	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/08 16:06
S182	188	method near5 sputtering near5 crystal.ti,ab,dm.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/08 16:06
S183	2	"20040169791"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/09 15:29
S184	0	S183 and intermittent	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/09 15:31
S185	0	S183 and blocking adj material	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/09 15:31

S186	0	S183 and blocking	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/09 15:35
S187	1	S183 and block	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/09 15:35
S188	6	(zinc adj tin adj oxide zinc- tin-oxide ZTO) near3 amorphous same channel and (tft ttft thin adj film adj transistor transistor mosfet channel)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/09 17:15
S189	6	(zinc adj tin adj oxide zinc- tin-oxide ZTO) near3 amorphous and (tft ttft thin adj film adj transistor transistor mosfet channel)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/09 17:17
S190	8	(zinc adj tin adj oxide zinc- tin-oxide ZTO ilmenite cubic adj spinel) near3 amorphous and (tft ttft thin adj film adj transistor transistor mosfet channel)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/09 17:21
S191	6	ternary adj compound near4 sputtering	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/09 17:25
S192	1	ternary adj compound near4 sputtering same amorphous	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/09 17:25
S193	3	("SnO.sub.2" near4 "ZnO") near4 sputtering same amorphous	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/09 17:26

S194	0	("SnO.sub.2" near4 "ZnO") near4 sputtering same crystalline	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/09 17:48
S195	0	("SnO.sub.2" near4 "ZnO") near4 sputtering same crystallinity	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/09 17:49
S196	0	("SnO.sub.2" near4 "ZnO") near4 sputtering same polycrystal	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/09 17:49
S197	0	("SnO.sub.2" near4 "ZnO") near4 sputtering same polycrystalline	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/09 17:49
S198	2	"20030185266".pn.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/09 17:50
S199	2	"20040127038".pn.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/09 17:53
S200	0	magnetron adj sputtering near4 amorphous	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/09 17:55
S201	139	magnetron adj sputtering near4 amorphous	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/09 17:55

S202	0	magnetron adj sputtering near4 amorphous near4 (ZnO "SnO.sub.2" zinc-tin-oxide)	US-PGPUB; USPAT; USOCR; FRRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/09 18:02
S203	0	magnetron adj sputtering near4 amorphous near4 (ZnO "SnO.sub.2" zinc-tin-oxide ternary adj compound)	US-PGPUB; USPAT; USOCR; FRRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/09 18:02
S204	1	magnetron adj sputtering near4 amorphous near4 (ZnO "SnO.sub.2" zinc-tin-oxide ternary adj compound ZTO ITO)	US-PGPUB; USPAT; USOCR; FRRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/09 18:03
S205	0	mobility near3 (zinc adj stannate "Zn.sub.2"\$1 near1 "SnO.sub.4")	US-PGPUB; USPAT; USOCR; FRRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/26 11:47
S206	0	mobility near3 (zinc adj stannate ("Zn.sub.2"\$1 near1 "SnO.sub.4"))	US-PGPUB; USPAT; USOCR; FRRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/26 11:47
S207	0	mobility near4 (zinc adj stannate ("Zn.sub.2"\$1 near1 "SnO.sub.4"))	US-PGPUB; USPAT; USOCR; FRRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/26 11:48
S208	0	mobility near8 (zinc adj stannate ("Zn.sub.2"\$1 near1 "SnO.sub.4"))	US-PGPUB; USPAT; USOCR; FRRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/26 11:48
S209	3	"20040127038"	US-PGPUB; USPAT; USOCR; FRRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/26 13:45

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